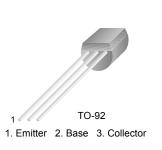


2N6517 NPN Epitaxial Silicon Transistor

Features

- High Voltage Transistor
- Collector Dissipation: P_C(max) = 625mW
- Complement to 2N6520
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



2N6517 — NPN Epitaxial Silicon Transistor

August 2010

Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Value	Units
V _{CBO}	Collector-Base Voltage	2N6517 2N6517C	350 400	V V
V _{CEO}	Collector-Emitter Voltage	2N6517 2N6517C	350 400	V V
V_{EBO}	Emitter-Base Voltage		6	V
۱ _C	Collector Current		500	mA
P _C	Collector Power Dissipation		625	mW
TJ	Junction Temperature		150	°C
T _{STG}	Storage Temperature		-55 ~ 150	°C

Electrical Characteristics T_a = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage				
020	2N6517	I _C = 100μA, I _E = 0	350		V
	2N6517C	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	400		V
BV _{CEO}	Collector-Emitter Breakdown Voltage *				
OLO	2N6517	I _C = 1mA, I _B = 0	350		V
	2N6517C	$I_{\rm C}$ = 1mA, $I_{\rm B}$ = 0	400		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E = 10μΑ, I _C = 0	6		V
I _{CBO}	Collector Cut-off Current	V _{CB} = 250V, I _E = 0		50	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5V, I _C = 0		50	nA
h _{FE}	DC Current Gain *				
	2N6517/2N6517C	V _{CE} = 10V, I _C = 1mA	20		
		$V_{CE} = 10V, I_{C} = 10mA$	30		
	2N6517/2N6517C	$V_{CF} = 10V, I_{C} = 30mA$	30	200	
	2N6517/2N6517C	$V_{CE} = 10V, I_{C} = 50mA$	20	200	
		$V_{CE} = 10V, I_{C} = 100mA$	15		
	2N6517C	$V_{CE} = 10V, I_{C} = 5mA$	50	200	

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2N6517 -
- NPN
Epitaxial
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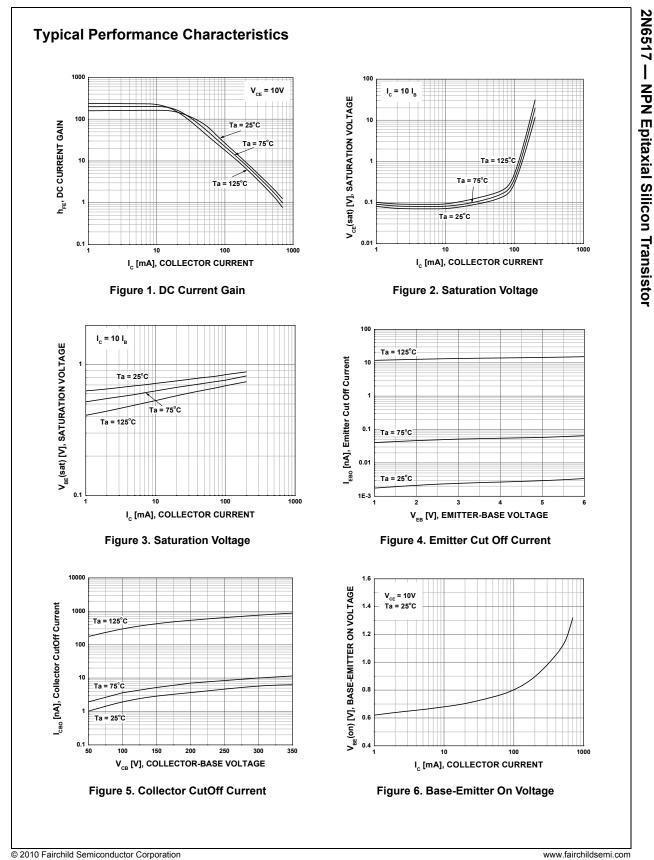
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Electrical Characteristics (Continued) $T_a = 25^{\circ}C$ unless otherwise noted

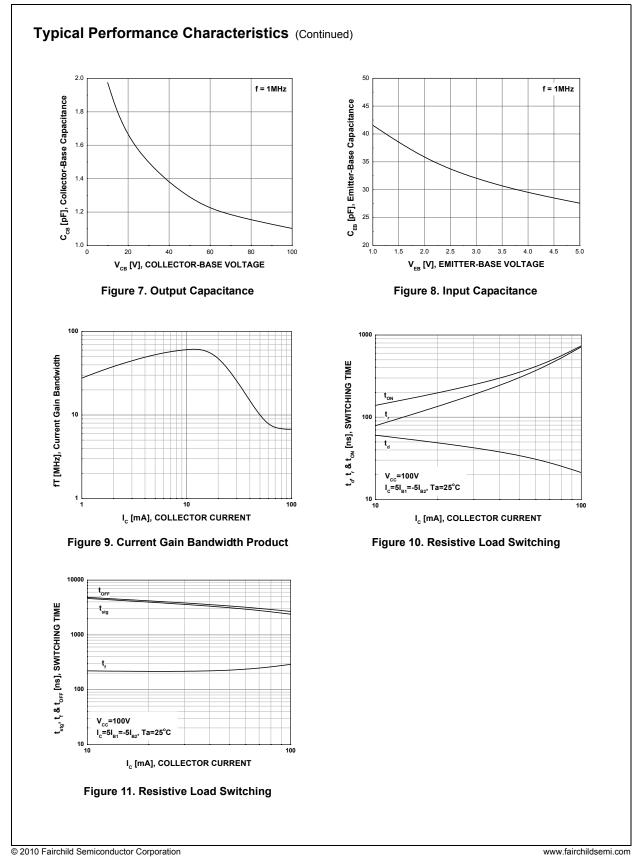
Symbol	Parameter	Conditions	Min.	Max.	Units
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA, I _B = 1mA		0.3	V
()		I _C = 20mA, I _B = 2mA		0.35	V
		$I_{C} = 30 \text{mA}, I_{B} = 3 \text{mA}$		0.5	V
		$I_{\rm C}$ = 50mA, $I_{\rm B}$ = 5mA		1	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10mA, I _B = 1mA		0.75	V
()		I _C = 20mA, I _B = 2mA		0.85	V
		I _C = 30mA, I _B = 3mA		0.9	V
C _{ob}	Output Capatitance	V_{CB} = 20V, I_{E} = 0, f = 1MHz		6	pF
f _T	Current Gain Bandwidth Product *	I_{C} = 10mA, V_{CE} = 20V, f = 20MHz	40	200	MHz
V _{BE(on)}	Base-Emitter On Voltage	I _C = 100mA, V _{CE} = 10V		2	V

* Pulse Test: Pulse Width $\leq 300 \mu s,$ Duty Cycle $\leq 2\%$

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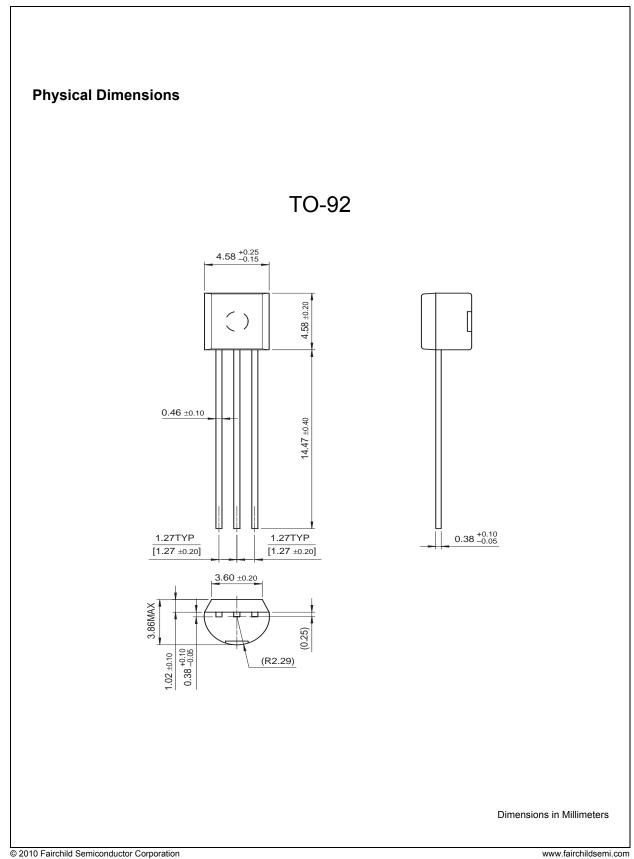


2N6517 Rev. B1



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